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Substitute for form 1449/PTO

Sheet 1

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complet if Known				
Application Number	10/683,822			
Filing Date	October 10, 2003			
First Named Inventor	Yong-Hang Zhang			
Art Unit	2815			
Examiner Name	Jerome Jackson Jr.			
Attorney Docket Number	9138-0137			

Examiner Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (f known)}	Publication Oate MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
///	1	^{US-} 6,506,618	01-14-2003	Kizuki et al	
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		FOREIGN	PATENT DOCU	MENTS		
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STA	STATEMENT BY APPLICANT		First Named Inventor	Yong-Hang Zhang	
44				Art Unit	2815
(Use as many sheets as necessary)		Examiner Name	Jerome Jackson Jr.		
Sheet	2	of	2	Attorney Docket Number	9138-0137

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
9	2	YANG, X. et al, "Molecular beam epitaxial growth of InGaAsN:Sb/GaAs quantum wells for long-wavelength," Applied Physics Letters, Jul 12, 1999, p 178-180, Vol 75, No 3	
	3	STORM, D. F. et al, "Surfactant effects of thallium in the epitaxial growth of indium," Journal of Applied Physics, May 1, 1999, p 6838-6842, Vol 85, No 9	
	4	KASPI, R. et al, "Surfactant-Mediated Growth of AlGaAs By Molecular Beam Epitaxy," Materials Research Society Symposium Proceedings, Apr 17-20,1995, p 79-85, Vol 379	
	5	YANG, et al, "Low threshold InGaAsN/GaAs single quantum well lasers grown by," Electronics Letters, June 24, 1999, p 1082-1083, Vol 35, No 13	

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Examiner // /	Date	2/05
Signature /// Jackson	Considered	407

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